Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (original): A method of fabricating a semiconductor device comprising:

providing a substrate;

sequentially forming a first organic layer, a sacrificial layer, and a second organic layer on the substrate;

performing a photolithography process for forming a predetermined pattern in the second organic layer;

utilizing the second organic layer as an etching mask for etching the sacrificial layer till a surface of the first organic layer is exposed, thus the predetermined pattern being transferred to the sacrificial layer;

utilizing the sacrificial layer as an etching mask for etching the first organic layer till a surface of the substrate is exposed, thereby the predetermined pattern being transferred to the first organic layer;

utilizing the sacrificial layer and the first organic layer as an etching mask for etching the substrate, thereby transferring the predetermined pattern to the substrate; and

removing the first organic layer by use of plasma.

2. (original): The method of claim 1 wherein the first organic layer is made of a material selected from the group consisting of low dielectric organic materials and spin-on glass (SOG).

3. (original): The method of claim 1 wherein the plasma is selected from the group

consisting of oxygen (O_2), nitrogen (N_2), hydrogen (H_2), argon (Ar), C_xF_y, $C_xH_yF_z$, and helium (He) plasma.

4. (previously presented): The method of claim 1 wherein the sacrificial layer is made of silicon nitride.

5. (previously presented): The method of claim 1 wherein the second organic layer is made of an organic photoresist material capable of absorbing light sources with wavelengths shorter than 248nm in deep UV regions.

6. (original): The method of claim 1 wherein the second organic layer is suitable for an e-beam lithography process.

7. (original): The method of claim 1 wherein the substrate is selected from the group consisting of a silicon substrate, a metal substrate, and a dielectric layer.

8. (previously presented): The method of claim 1 wherein the sacrificial layer is made of silicon oxide.

9. (canceled)

10. (previously presented): The method of claim 1 wherein the sacrificial layer is removed concurrently while etching the substrate.

11. (canceled)

12. (previously presented): The method of claim 1 wherein the method further comprises forming an anti-reflection layer on the sacrificial layer before forming the second

organic layer.

13. (previously presented): The method of claim 12 wherein the anti-reflection layer comprises organic materials.

14. (previously presented): The method of claim 12 wherein the anti-reflection layer comprises inorganic materials.